

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 – 19. (canceled)

20. (previously presented) A semiconductor component comprising a semiconductor chip made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises;

 a reinforcing system formed directly on the doped silicon substrate in an open grid structure within a contact window, wherein the open grid structure forms individual grid openings that leave portions of the doped silicon substrate exposed within the contact window; and

 a connection metallization formed in between the open grid structure of the reinforcing system and directly on the doped silicon substrate at the exposed portions of the doped silicon substrate in the contact window;

 wherein the reinforcing system and the connection metallization have different physical properties.

21. (previously presented) A semiconductor component as claimed in claim 20, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

22. (previously presented) A semiconductor component as claimed in claim 20, characterized in that the grid structure is formed so as to be an open groove structure.

23. (previously presented) A semiconductor component as claimed in claim 20, characterized in that the grid structure may be formed so as to be an open tube structure.

24. (previously presented) A semiconductor component as claimed in claim 20, characterized in that the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

25. (previously presented) A semiconductor component as claimed in claim 20, wherein the open grid structure comprises grid lands and wherein a ratio of height, h, to width, b, of the grid lands is in the range of 1:25 to 1:50.

26. (previously presented) A semiconductor component as claimed in claim 20, wherein the open grid structure comprises grid lands and grid openings and wherein the ratio between the area of the grid lands and the area of the grid openings is greater than 70%.

27. (previously presented) A semiconductor component as claimed in claim 20, wherein the open grid structure of the reinforcing system comprises oxide lands formed directly on the doped silicon substrate.

28. (previously presented) A semiconductor component comprising:

discrete semiconductor device comprising:

a silicon substrate having an emitter and a base;

the emitter having an emitter contact formed thereon, the emitter contact comprising:

a reinforcing system formed directly on the emitter in an open grid structure within an emitter contact window, wherein the open grid structure forms individual grid openings that leave portions of the emitter exposed within the emitter contact window; and

a connection metallization formed in between the open grid structure of the reinforcing system and directly on the emitter;

wherein the reinforcing system and the connection metallization have different physical properties;

the base having a base contact formed thereon, the base contact comprising having:

a reinforcing system formed directly on the base in an open grid structure within a base contact window, wherein the open grid structure forms individual grid openings that leave portions of the base exposed within the base contact window; and

a connection metallization formed in between the open grid structure of the reinforcing system and directly on the base;

wherein the reinforcing system and the connection metallization have different physical properties

a leadframe having connection pins; and

a bond wire connected between the emitter contact and a connection pin of the leadframe; and

a bond wire connected between the base contact and a connection pin of the leadframe.

29. (previously presented) A semiconductor component as claimed in claim 28, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

30. (previously presented) A semiconductor component as claimed in claim 28, characterized in that the grid structure is formed so as to be an open groove structure.

31. (previously presented) A semiconductor component as claimed in claim 28, characterized in that the grid structure may be formed so as to be an open tube structure.

32. (previously presented) A semiconductor component as claimed in claim 28, characterized in that the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

33. (previously presented) A semiconductor component as claimed in claim 28, wherein the open grid structure of the reinforcing system comprises oxide lands formed directly on the silicon substrate.